

HD74HC640, HD74HC643

Octal Bus Transceivers (with 3-state outputs)

REJ03D0637-0200
 (Previous ADE-205-517)
 Rev.2.00
 Mar 30, 2006

Description

Each device has an active enable \overline{G} and a direction control input, DIR. When DIR is high, data flows from the A inputs to the B outputs. When DIR is low, data flows from the B inputs to the A outputs. The HD74HC640 transfers inverted data from one bus to other and the HD74HC643 transfers inverted data from the A bus to the B bus and true data from the B bus to the A bus.

Features

- High Speed Operation: $t_{pd} = 12 \text{ ns typ (} C_L = 50 \text{ pF)}$
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2 \text{ to } 6 \text{ V}$
- Low Input Current: $1 \mu\text{A max}$
- Low Quiescent Supply Current: $I_{CC} \text{ (static)} = 4 \mu\text{A max (} T_a = 25^\circ\text{C)}$
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HC640P	DILP-20 pin	PRDP0020AC-B (DP-20NEV)	P	—
HD74HC640FPEL	SOP-20 pin (JEITA)	PRSP0020DD-B (FP-20DAV)	FP	EL (2,000 pcs/reel)
HD74HC640RPEL HD74HC643RPEL	SOP-20 pin (JEDEC)	PRSP0020DC-A (FP-20DBV)	RP	EL (1,000 pcs/reel)

Note: Please consult the sales office for the above package availability.

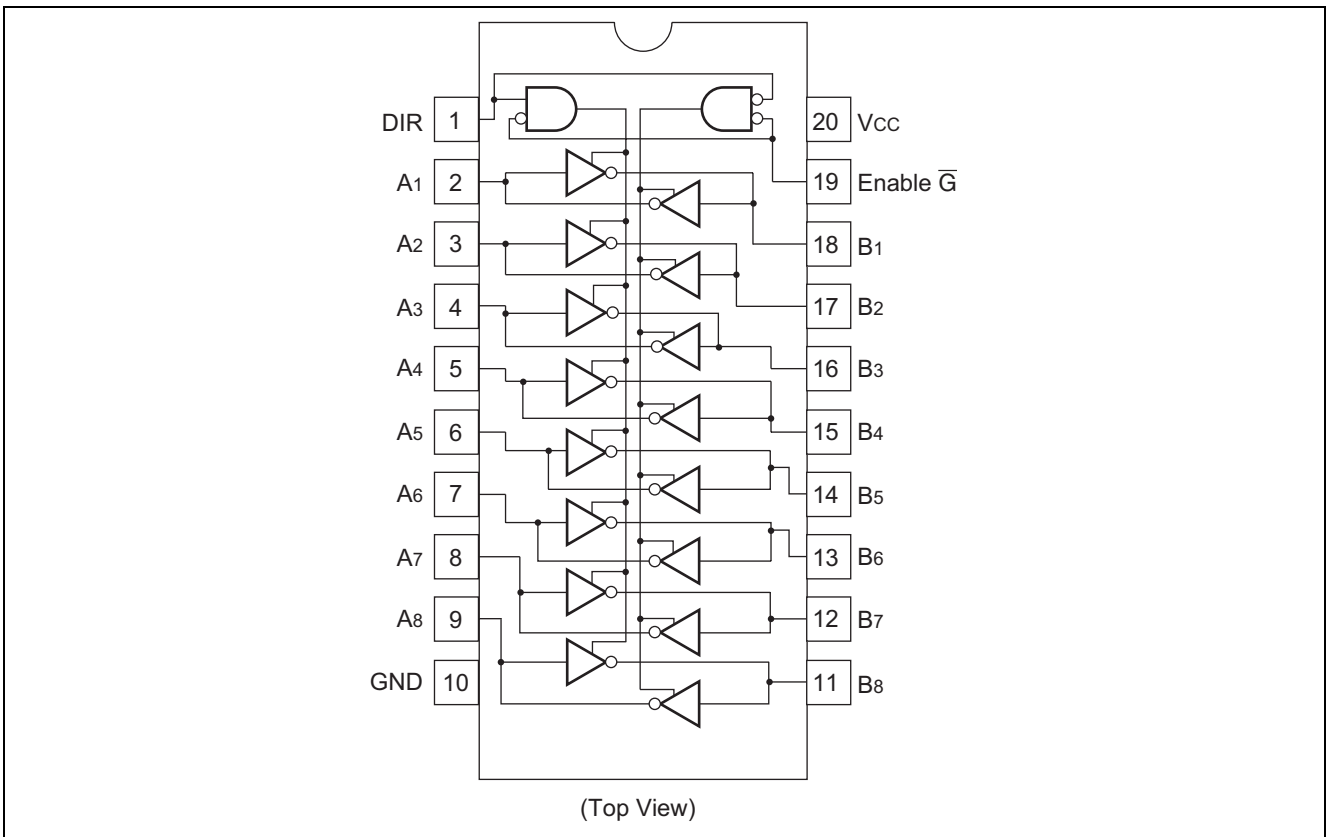
Function Table

Control Inputs		Operation	
\overline{G}	DIR	HD74HC640	HD74HC643
L	L	\overline{B} data to A bus	B data to A bus
L	H	\overline{A} data to B bus	\overline{A} data to B bus
H	X	Isolation	Isolation

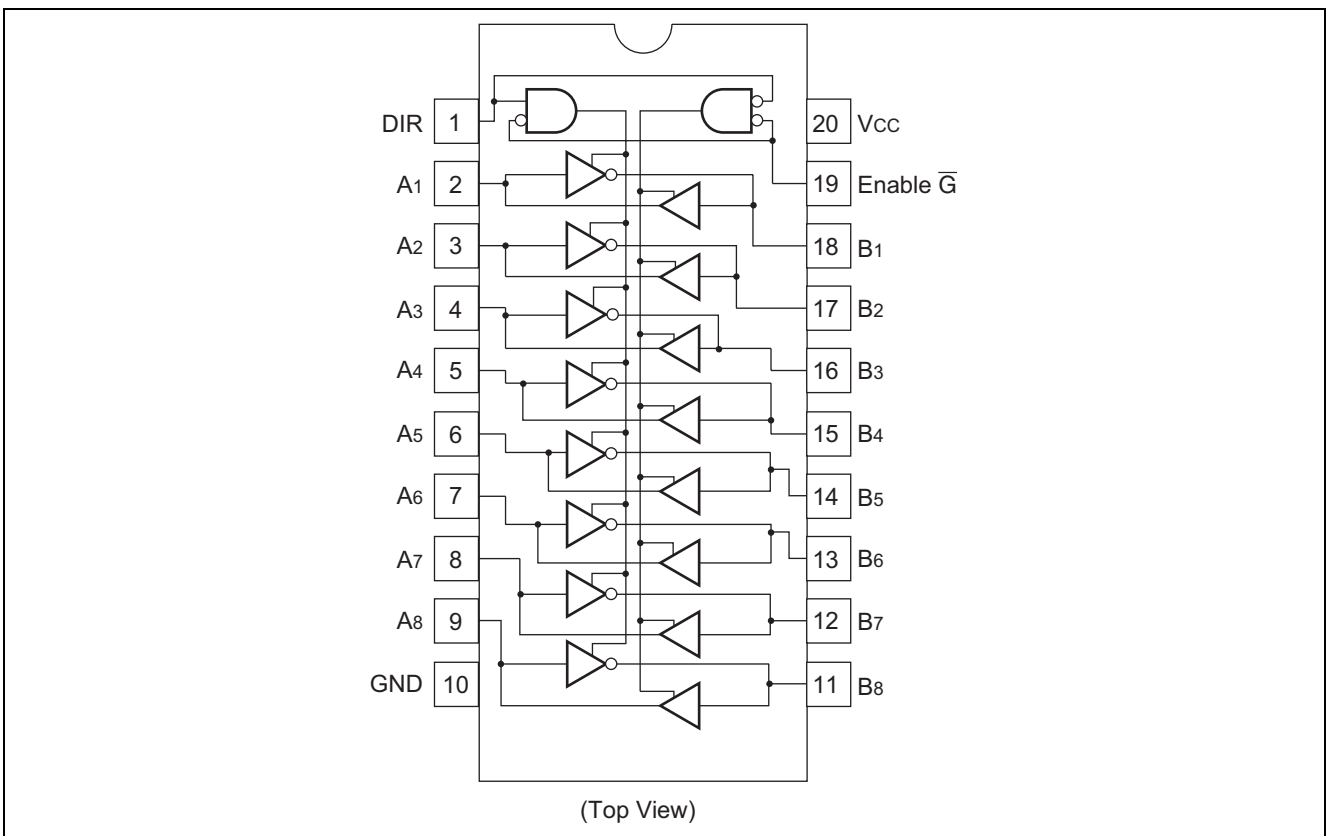
H : high level
 L : low level
 X : irrelevant

Pin Arrangement

HD74HC640

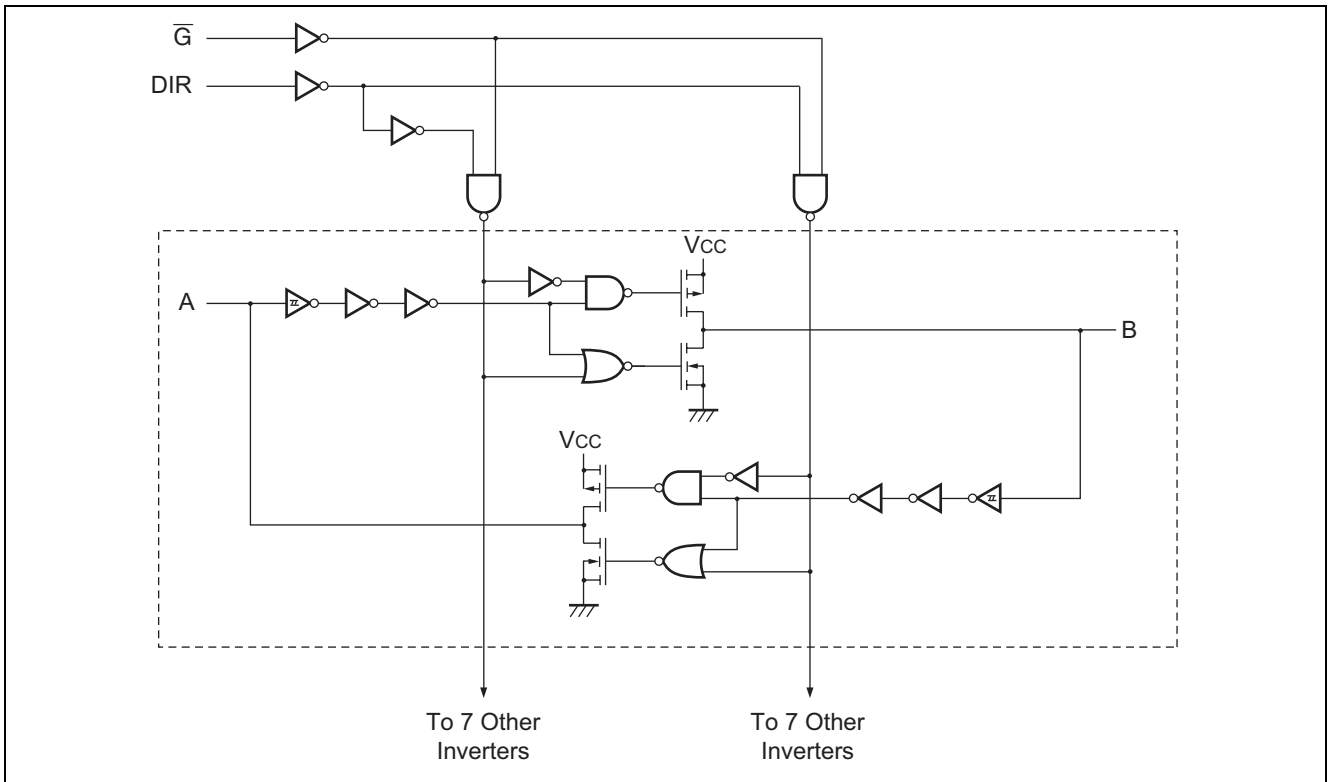


HD74HC643

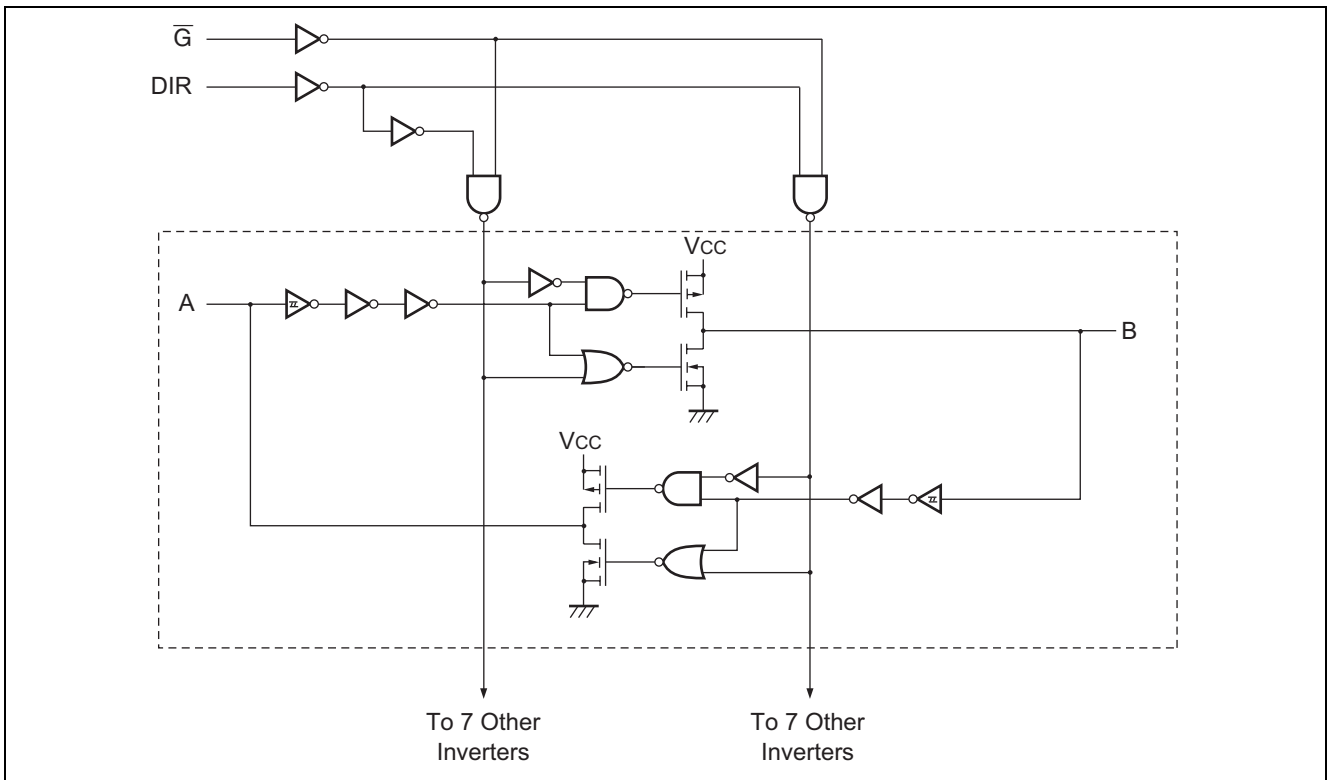


Logic Diagram

HD74HC640



HD74HC643



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit
Supply voltage range	V_{CC}	-0.5 to 7.0	V
Input / Output voltage	V_{IN}, V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
Input / Output diode current	I_{IK}, I_{OK}	± 20	mA
Output current	I_O	± 35	mA
V_{CC} , GND current	I_{CC} or I_{GND}	± 75	mA
Power dissipation	P_T	500	mW
Storage temperature	T_{stg}	-65 to +150	°C

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V_{CC}	2 to 6	V	
Input / Output voltage	V_{IN}, V_{OUT}	0 to V_{CC}	V	
Operating temperature	T_a	-40 to 85	°C	
Input rise / fall time ^{*1}	t_r, t_f	0 to 1000	ns	$V_{CC} = 2.0$ V
		0 to 500		$V_{CC} = 4.5$ V
		0 to 400		$V_{CC} = 6.0$ V

Note: 1. This item guarantees maximum limit when one input switches.
Waveform: Refer to test circuit of switching characteristics.

Electrical Characteristics

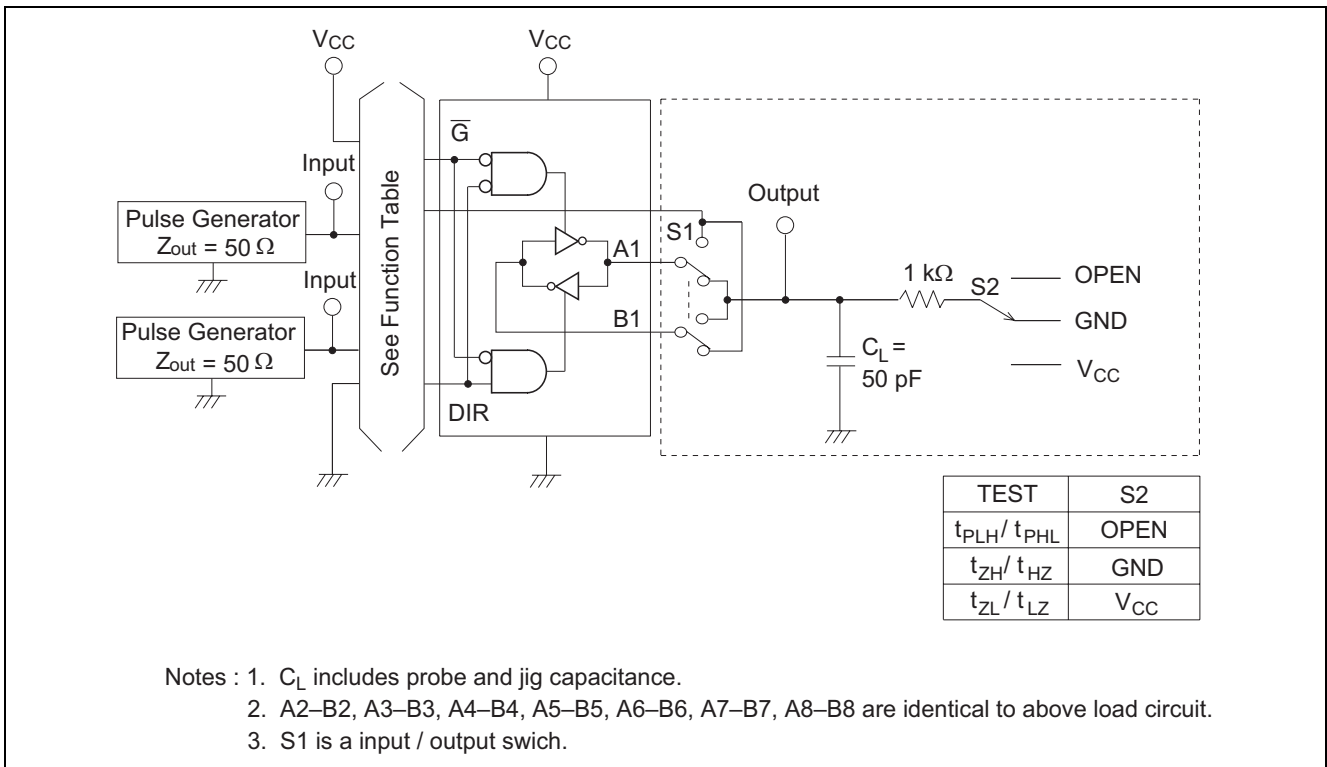
Item	Symbol	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40 \text{ to } +85^\circ\text{C}$		Unit	Test Conditions		
			Min	Typ	Max	Min	Max				
Input voltage	V_{IH}	2.0	1.5	—	—	1.5	—	V			
		4.5	3.15	—	—	3.15	—				
		6.0	4.2	—	—	4.2	—				
	V_{IL}	2.0	—	—	0.5	—	0.5	V			
		4.5	—	—	1.35	—	1.35				
		6.0	—	—	1.8	—	1.8				
Output voltage	V_{OH}	2.0	1.9	2.0	—	1.9	—	V	$V_{in} = V_{IH}$ or V_{IL}	$I_{OH} = -20$ μA	
		4.5	4.4	4.5	—	4.4	—			$I_{OH} = -6$ mA	
		6.0	5.9	6.0	—	5.9	—			$I_{OH} = -7.8$ mA	
		4.5	4.18	—	—	4.13	—				
		6.0	5.68	—	—	5.63	—				
	V_{OL}	2.0	—	0.0	0.1	—	0.1	V	$V_{in} = V_{IH}$ or V_{IL}	$I_{OL} = 20$ μA	
		4.5	—	0.0	0.1	—	0.1				
		6.0	—	0.0	0.1	—	0.1				
		4.5	—	—	0.26	—	0.33				$I_{OL} = 6$ mA
		6.0	—	—	0.26	—	0.33				$I_{OL} = 7.8$ mA
Off-state output current	I_{OZ}	6.0	—	—	± 0.5	—	± 5.0	μA	$V_{in} = V_{IH}$ or V_{IL} , $V_{out} = V_{CC}$ or GND		
Input current	I_{in}	6.0	—	—	± 0.1	—	± 1.0	μA	$V_{in} = V_{CC}$ or GND		
Quiescent supply current	I_{CC}	6.0	—	—	4.0	—	40	μA	$V_{in} = V_{CC}$ or GND, $I_{out} = 0$ μA		

Switching Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

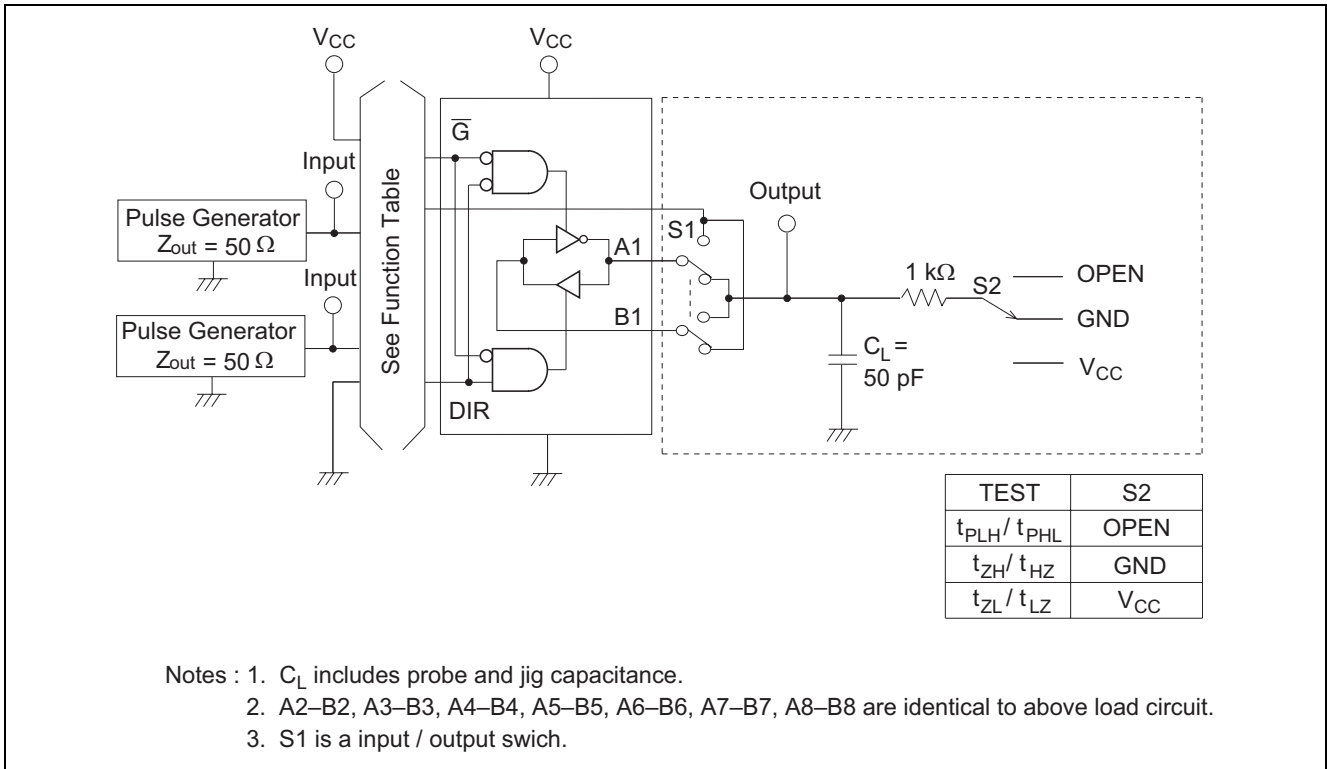
Item	Symbol	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40 \text{ to } +85^\circ\text{C}$		Unit	Test Conditions
			Min	Typ	Max	Min	Max		
Propagation delay time	t_{PHL}	2.0	—	—	90	—	115	ns	
		4.5	—	12	18	—	23		
		6.0	—	—	15	—	20		
	t_{PLH}	2.0	—	—	90	—	115	ns	
		4.5	—	12	18	—	23		
		6.0	—	—	15	—	20		
Output enable time	t_{ZL}	2.0	—	—	230	—	290	ns	
		4.5	—	15	46	—	58		
		6.0	—	—	39	—	49		
	t_{ZH}	2.0	—	—	230	—	290	ns	
		4.5	—	15	46	—	58		
		6.0	—	—	39	—	49		
Output disable time	t_{LZ}	2.0	—	—	215	—	270	ns	
		4.5	—	17	43	—	54		
		6.0	—	—	37	—	46		
	t_{HZ}	2.0	—	—	215	—	270	ns	
		4.5	—	17	43	—	54		
		6.0	—	—	37	—	46		
Output rise/fall time	t_{TLH}	2.0	—	—	60	—	75	ns	
	t_{THL}	4.5	—	4	12	—	15		
	t_{THL}	6.0	—	—	10	—	13		
Input capacitance	C_{in}	—	—	5	10	—	10	pF	

Test Circuit

HD74HC640



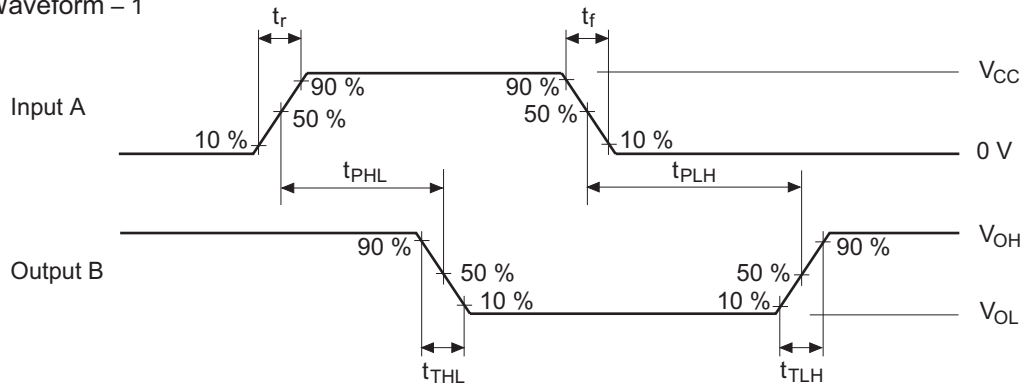
HD74HC643



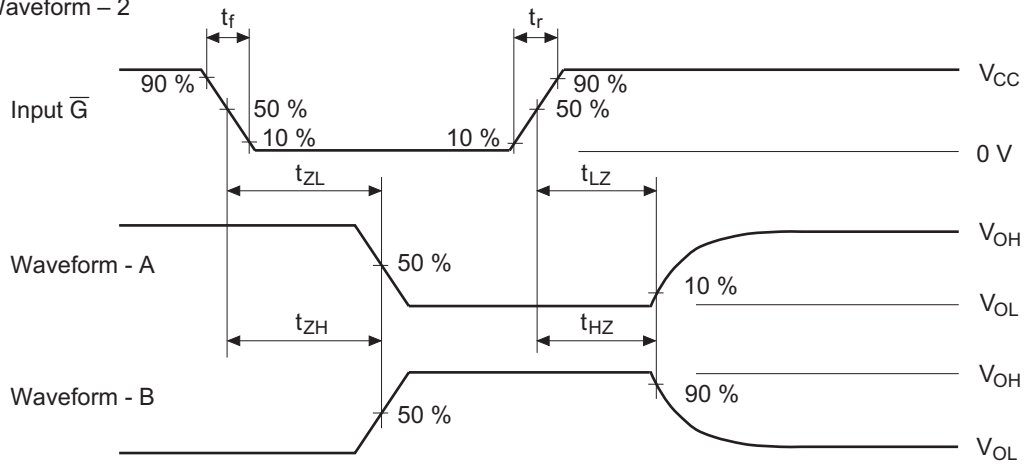
Waveforms

HD74HC640

• Waveform – 1



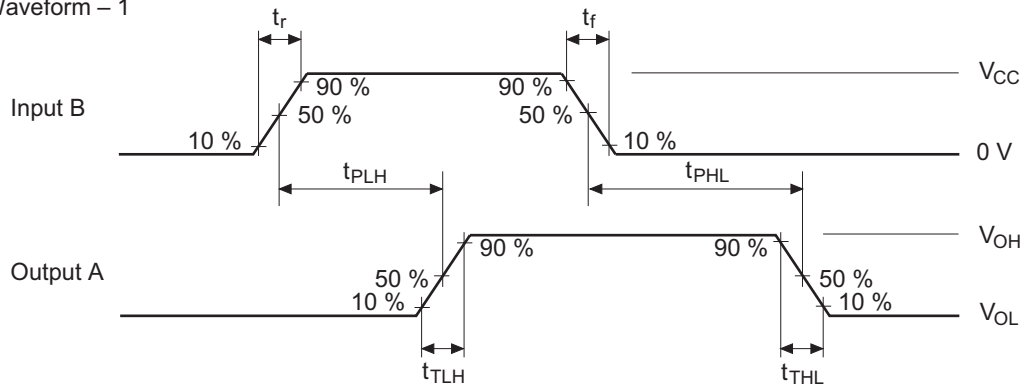
• Waveform – 2



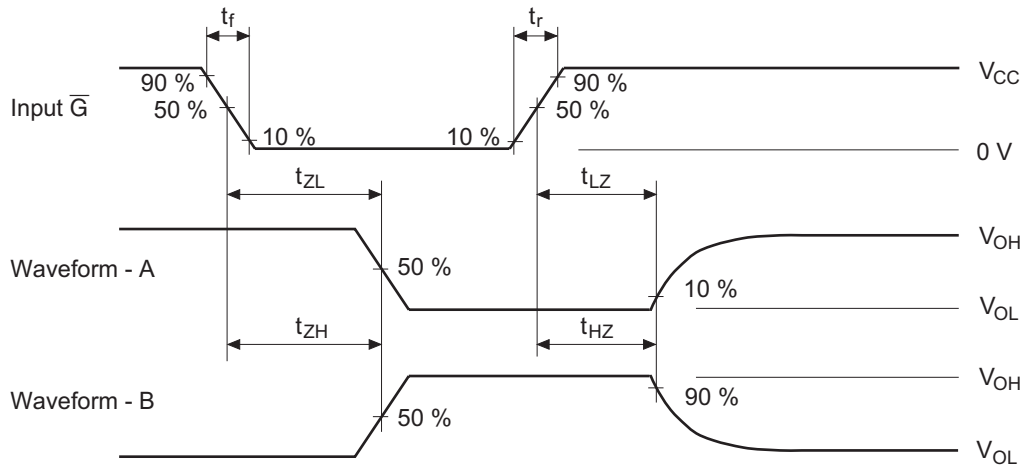
- Notes :
1. Input waveform : $PRR \leq 1 \text{ MHz}$, duty cycle 50%, $t_r \leq 6 \text{ ns}$, $t_f \leq 6 \text{ ns}$
 2. Waveform - A is for an output with internal conditions such that the output is low except when disabled by the output control.
 3. Waveform - B is for an output with internal conditions such that the output is high except when disabled by the output control.
 4. The output are measured one at a time with one transition per measurement.

HD74HC643

• Waveform – 1

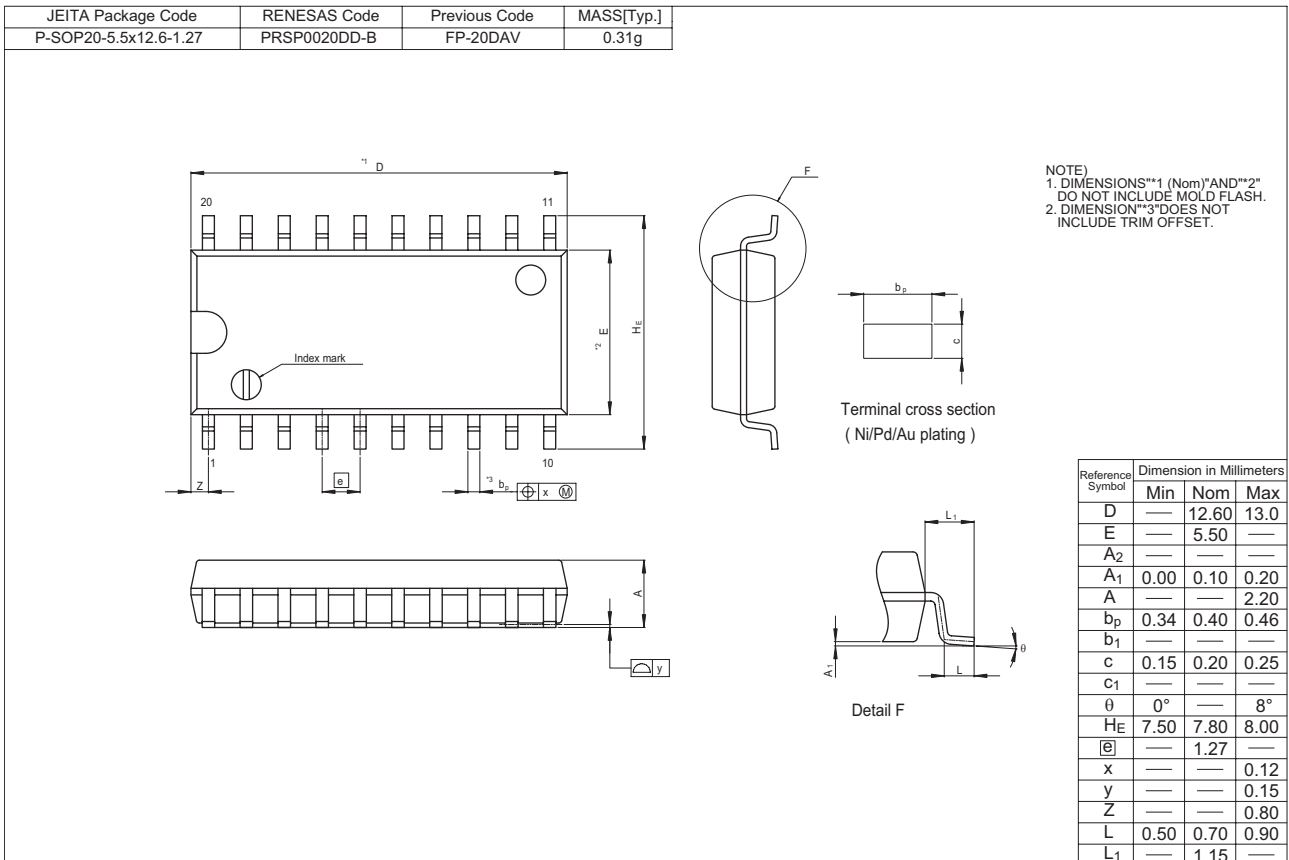
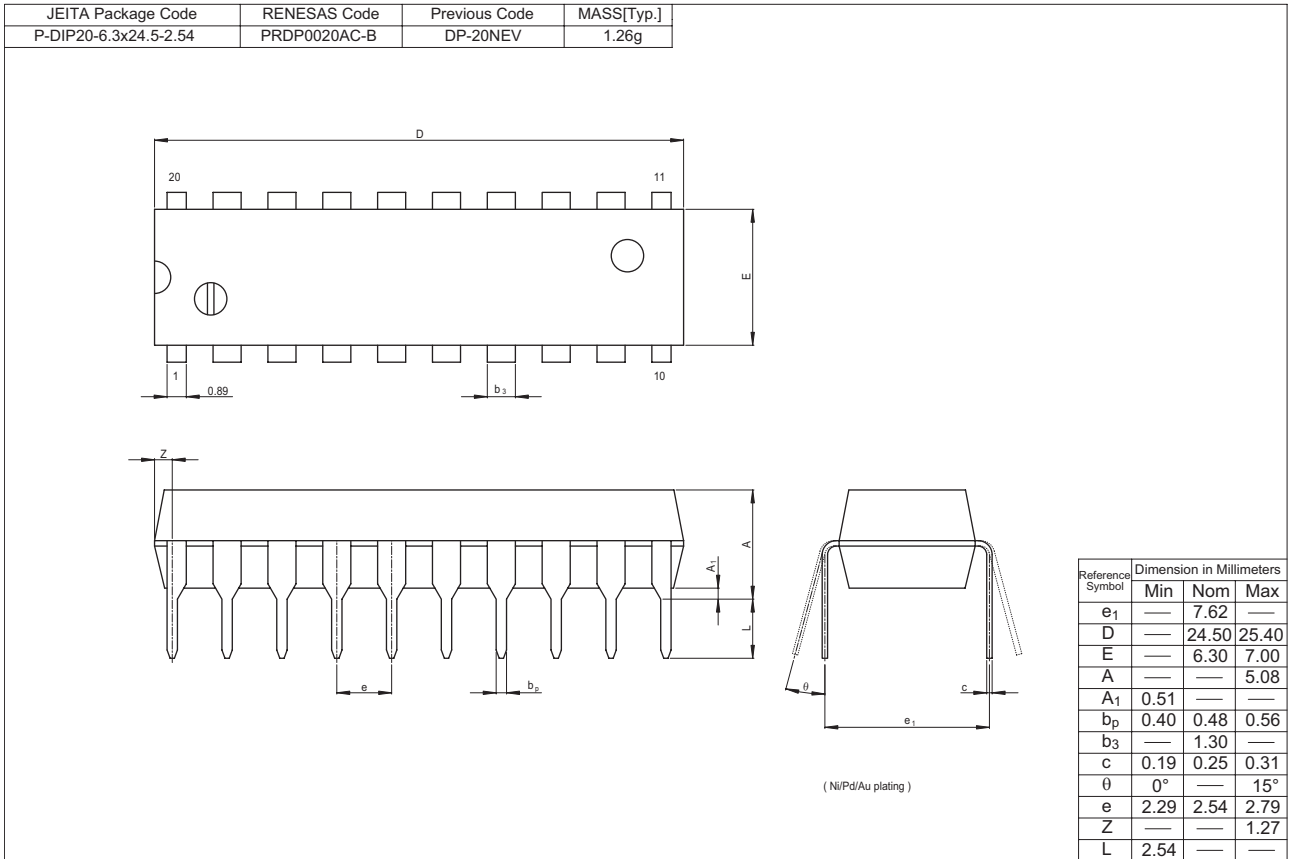


• Waveform – 2



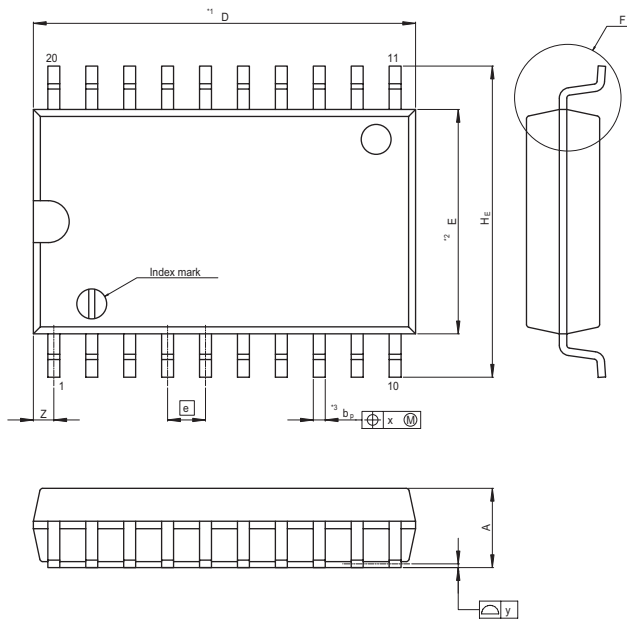
- Notes :
1. Input waveform : PRR \leq 1 MHz, duty cycle 50%, $t_r \leq$ 6 ns, $t_f \leq$ 6 ns
 2. Waveform - A is for an output with internal conditions such that the output is low except when disabled by the output control.
 3. Waveform - B is for an output with internal conditions such that the output is high except when disabled by the output control.
 4. The output are measured one at a time with one transition per measurement.

Package Dimensions

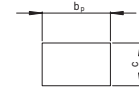


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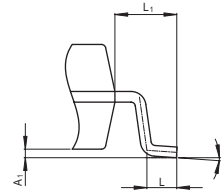
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-SOP20-7.5x12.8-1.27	PRSP0020DC-A	FP-20DBV	0.52g



NOTE)
 1. DIMENSIONS**1 (Nom)**AND**2*
 @ DO NOT INCLUDE MOLD FLASH.
 2. DIMENSION**3*DOES NOT
 @ INCLUDE TRIM OFFSET.



Terminal cross section
(Ni/Pd/Au plating)



Detail F

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	12.80	13.2
E	—	7.50	—
A ₂	—	—	—
A ₁	0.10	0.20	0.30
A	—	—	2.65
b _p	0.34	0.40	0.46
b ₁	—	—	—
c	0.20	0.25	0.30
c ₁	—	—	—
θ	0°	—	8°
H _E	10.00	10.40	10.65
ⓐ	—	1.27	—
x	—	—	0.12
y	—	—	0.15
Z	—	—	0.935
L	0.40	0.70	1.27
L ₁	—	1.45	—

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